

N-Channel 60-V(D-S) MOSFET

V(BR)DSS	RDS(on)MAX	ID
60 V	95mΩ@10V	3A
	100mΩ@4.5V	

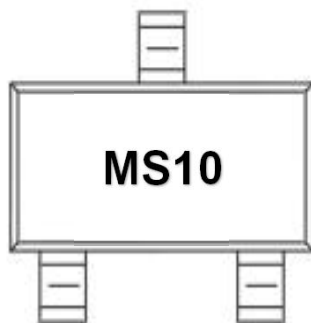
FEATURE

※ TrenchFET Power MOSFET

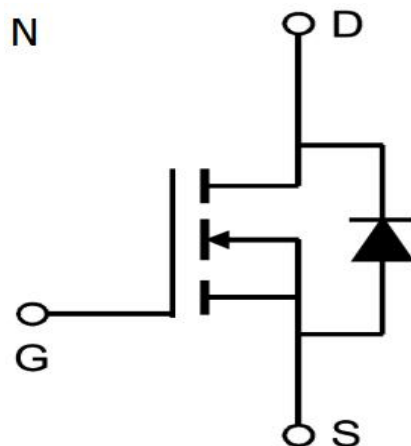
APPLICATION

※ Load Switch for Portable Devices
 ※ DC/DC Converter

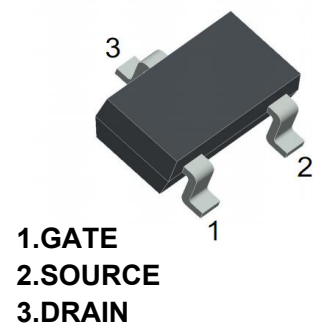
MARKING



Equivalent Circuit



SOT-23



Maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	60	V
Gate-Source Voltage	VGS	±20	
Continuous Drain Current	ID	3	A
Pulsed Diode Current	IDM	10	
Continuous Source-Drain Current(Diode Conduction)	IS	0.8	
Power Dissipation	PD	1.25	W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	357	℃/W
Operating Junction	TJ	150	℃
Storage Temperature	TSTG	-55~+150	℃

MOSFET ELECTRICAL CHARACTERISTICS

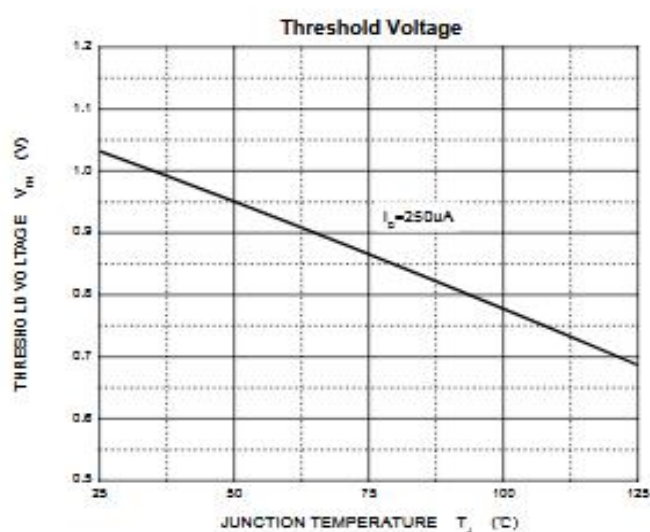
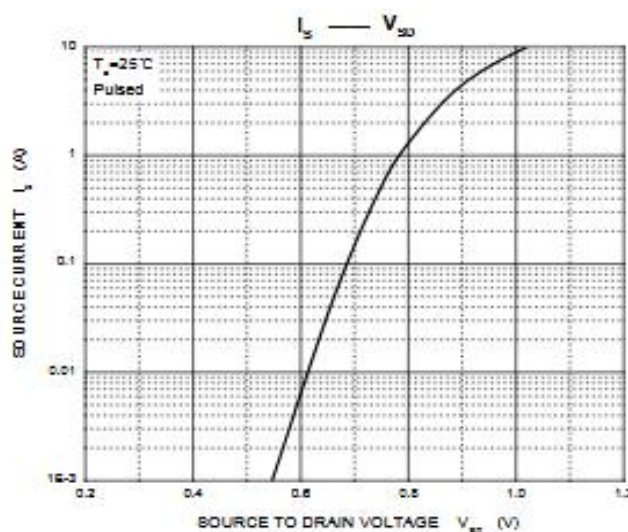
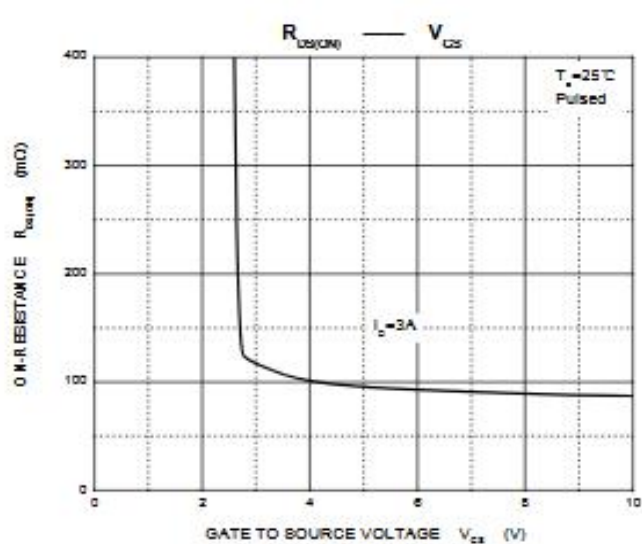
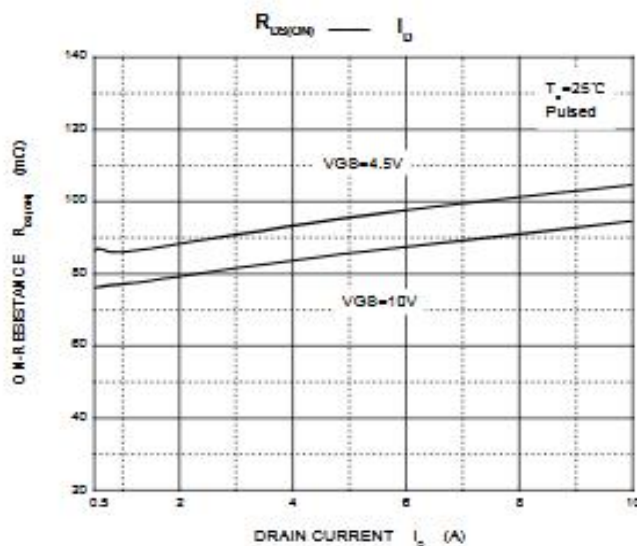
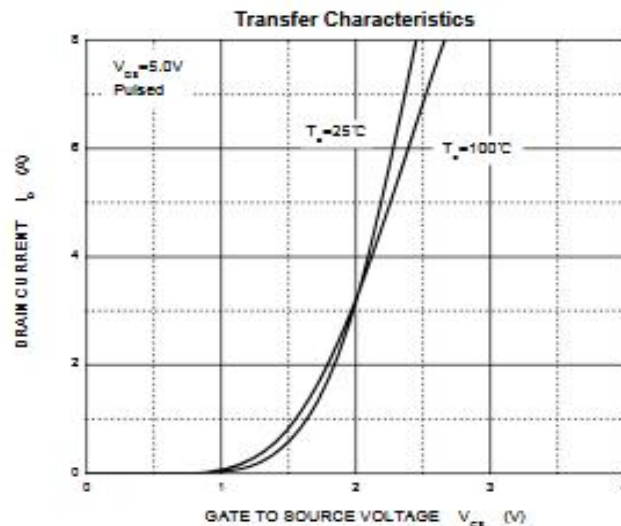
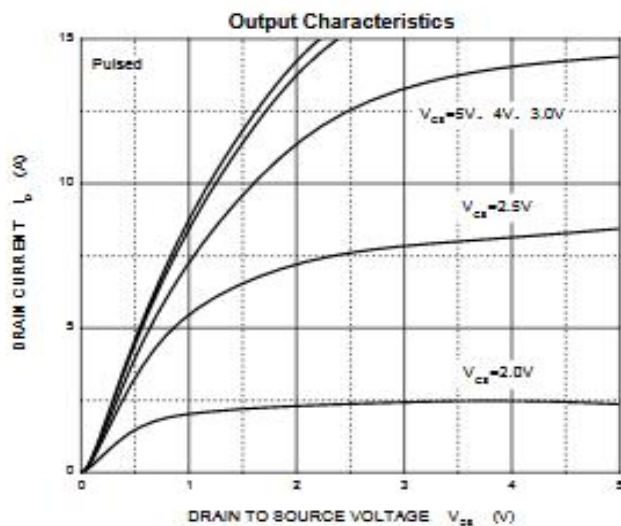
Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)

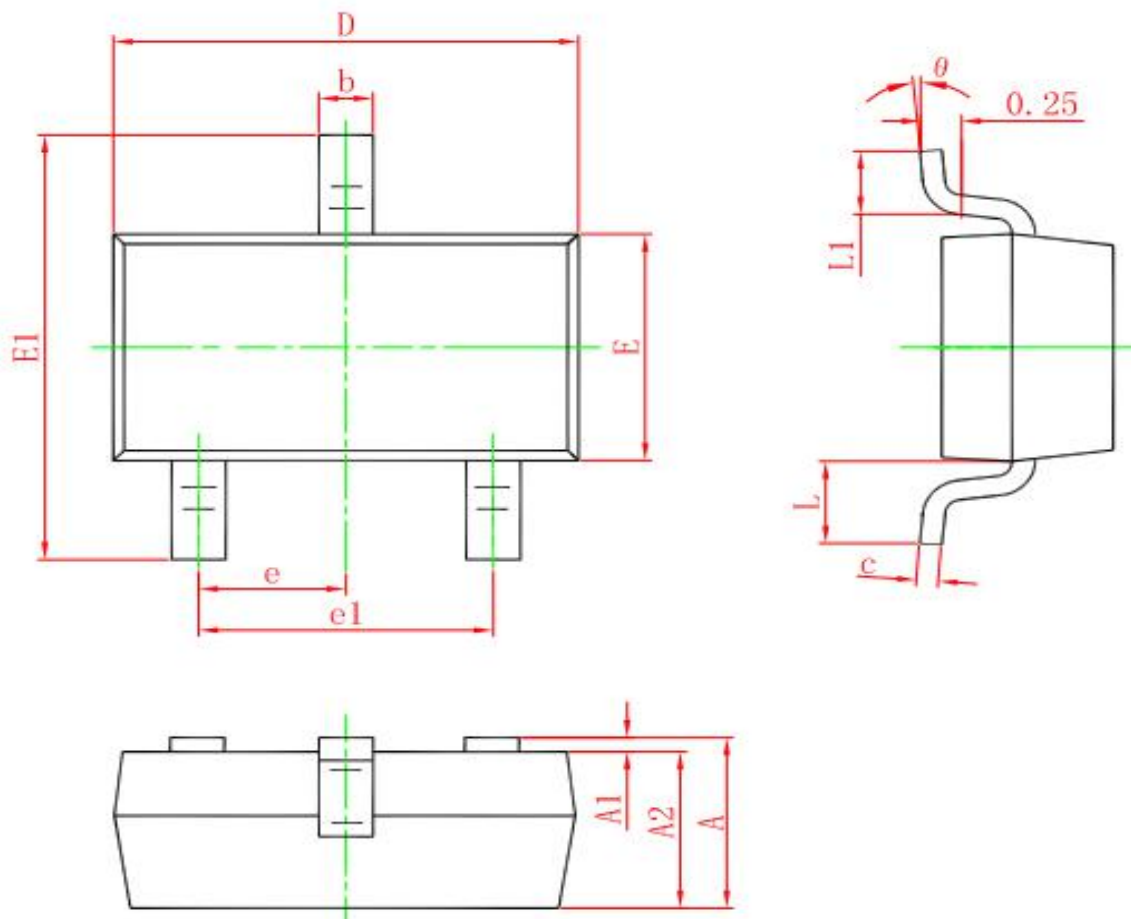
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = 250μA	60			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = 250μA	0.9		2	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±20V			±100	nA
Zero gate voltage drain current	IDSS	VDS = 60V, VGS =0V			1	μA
Drain-source on-state resistancea	RDS(on)	VGS = 10V, ID = 3 A		72	95	mΩ
		VGS = 4.5V, ID = 2 A		82	100	mΩ
Forward transconductancea	gfs	VDS = 4.5V, ID = 3A		7		S
Diode forward voltage	VSD	IS=1A,VGS=0V		0.8	1.2	V
Dynamic						
Input capacitance	Ciss	VDS = 10V,VGS =0V, f=1MHz		247		pF
Output capacitance	Coss			34		pF
Reverse transfer capacitanceb	Crss			20		pF
Total gate charge	Qg	VDS = 10V,VGS = 4.5V, ID = 3A		6	4.5	nC
Gate-source charge	Qgs			1		nC
Gate-drain charge	Qgd			1.3		nC
Gate resistance	Rg	f=1MHz		5		Ω
Switchingb						
Turn-on delay time	td(on)	VDD= 10V RL=10Ω, ID ≈ 1A, VGEN= 4.5V,Rg=6Ω		7	15	ns
Rise time	tr			15	20	ns
Turn-off delay time	td(off)			15	25	ns
Fall time	tf			10	20	ns
Drain-source body diode characteristics						
Continuous Source-Drain Diode Current	IS	Tc=25℃			1.2	A
Pulsed Diode forward Curren	ISM				20	A

Note :

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



SOT-23 PACKAGE OUTLINE DIMENSIONS


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°